		TOTAL DOSE TEST PLAN NO.							Iss	Issue No. Rev.										
ESCC												Date Date								
						1						1	Page 1/				2			
ESCC Component No.					Con	mponent Designation:						_	Irradiation Spec. No.							
				3		r						4	IS	S.	_		Rev.			5
Specifications					Acceptance Sample						e Size:	Size:				Project/ Programme				
Generic Iss. Rev.						Diffusion Control						l Devic	Devices:							
Detail Iss. Rev.				6	Lot 7						8			1				9		
FAMILY:				!_		GROUP							PA			PACI	PACKAGE:			
				Г	10	-							11					12		
Manufacturer: Nam	ne'				. •	Toot Housey Names									Originator:				1	
Address:						Test House: Name: Address:										Name:				
				Γ.	13								14			Telephone:				15
	IRRADIATION:				Irradiation Measurement Interval Level of Interest								it		•					
Facility: Single Bias					Bias	sed Circuit Ref:														
Source:	: Multiple 🔲 Unb					iased $\square$	Su	pply V	oltage:											
16	3		17	1	Tem	p: °CDuration							1	8						19
Single Irradiation	-				Multiple					$\prod_{i}$				_	T	6	7			
			ł		rradiation Steps				1	2	+	3	4	5	+	6	7	8	1	
Dose (krad(Si)):	4.					ad(Si))			+	$\dashv$				+				1		
Dose Rate (rad(Si)s <sup>-1</sup> ):  Exposure Time:  20						te (rad(Si)s <sup>-1</sup> ) e Time				+	+				+				1	21
	ne:			Схро	Suit	e iiiie	Anneal Test?:								<u> </u>	1 - '				
Irradiation Conditions:				Bias Circuit Ref:				l					ias Circuit Ref:							
Biased (Remote Test):  Unbiased (Remote Test):				Supply Voltages:				1 =					upply Voltages:							
In-Situ Test			_	Temp			22	1					Duration:					23		
Electrical Parameters to be tested																				<u> </u>
																				24
No. Characteristics					s	Symbol	Spec. and/or Test Method				Τ.	est C	onditi	ons	S					
								rest Method												

		тот	AL DOSE TEST PLAN NO.		Issue No.	Rev.	
ESCC					Date	Date	
Irradiation Test Se	equence			1	Page 1/		2
Tradiction rest oc	, que no c						25
Test Step	Description		Requirements				
							1
Remarks							26